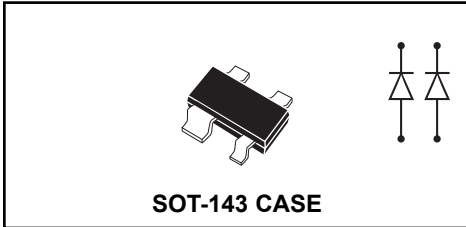


CMFD2004i

**DUAL ISOLATED HIGH VOLTAGE
SILICON SWITCHING DIODES**



CentralTM

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMFD2004i consists of two electrically Isolated high voltage switching diodes packaged in an epoxy molded SOT-143 surface mount case. This device is designed for switching applications requiring dual high voltage diodes.

MARKING CODE: CJP

MAXIMUM RATINGS: ($T_A=25\text{ }^\circ\text{C}$)

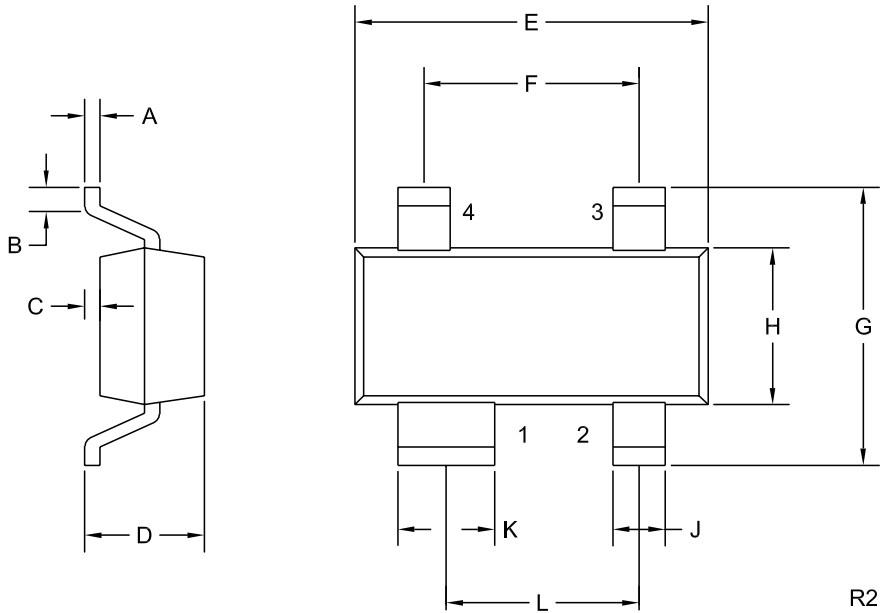
	SYMBOL		UNITS
Continuos Reverse Voltage	V_R	240	V
Peak Repetitive Reverse Voltage	V_{RRM}	300	V
Peak Repetitive Reverse Current	I_O	200	mA
Continuous Forward Current	I_F	225	mA
Peak Repetitive Forward Current	I_{FRM}	450	mA
Forward Surge Current, $t_p=1\mu s$	I_{FSM}	4.0	A
Forward Surge Current, $t_p=1s$	I_{FSM}	1.0	A
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	357	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25\text{ }^\circ\text{C}$ unless otherwise noted)

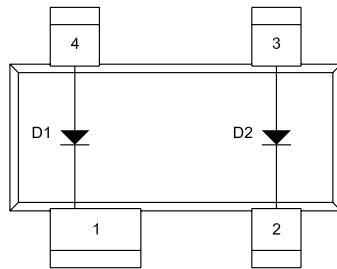
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=240V$		100	nA
I_R	$V_R=240V, T_A=150\text{ }^\circ\text{C}$		100	μA
BV_R	$I_R=100\text{ }\mu\text{A}$	300		V
V_F	$I_F=100\text{mA}$		1.0	V
C_T	$V_R=0V, f=1.0\text{MHz}$		5.0	pF
t_{rr}	$I_F=I_R=30\text{mA}, I_{rr}=3.0\text{mA}, R_L=100\Omega$		50	ns

**DUAL ISOLATED HIGH VOLTAGE
SILICON SWITCHING DIODES**

SOT-143 CASE - MECHANICAL OUTLINE



R2



LEAD CODE:

- 1) CATHODE D1
- 2) CATHODE D2
- 3) ANODE D2
- 4) ANODE D1

MARKING CODE: CJP

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.006	0.08	0.15
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	-	0.045	-	1.14
E	0.110	0.120	2.79	3.04
F	0.075		1.90	
G	-	0.098	-	2.50
H	0.047	0.055	1.19	1.40
J	0.014	0.020	0.36	0.50
K	0.030	0.037	0.76	0.93
L	0.067		1.70	

SOT-143 (REV: R2)